

**DESCRIPTION**

This is a high radiance InGaAs IR LED for applications requiring 1050 nm emission and a fast response time.

**FEATURES**

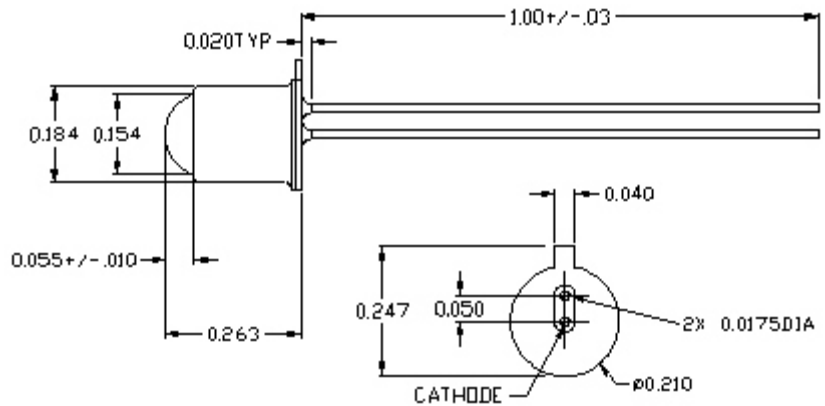
- 12 Degree Half Angle of light emission
- High Electrical Bandwidth/Fast response time
- High Reliability
- Hermetic Package

**ABSOLUTE MAXIMUM RATINGS**

- Storage temperature.....-65°C to +125°C
- Case operating temperature.. -40°C to +85°C
- Lead solder temperature..... 260°C, 10 seconds
- Continuous forward current..... 100 mA
- Reverse Voltage..... 3 Volts

**OUTLINE DIMENSIONS**

Tolerances are +/-0.005 inches, except as noted



**Pinout**

1. Cathode
2. Anode

The case is electrically isolated from the pins.

**ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)**

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Forward Voltage	I <sub>f</sub> = 100 mA	V <sub>f</sub>		1.2	2.0	Volts
Reverse Voltage	I <sub>r</sub> = 10 μA	BVR	3.0			Volts
Half Angle at Half Power		θ <sub>1/2</sub>		6	12	DEG
Capacitance	V <sub>r</sub> = 0 V, f = 1 MHz	C		70		pF
Total Optical Power	I <sub>f</sub> = 100 mA	P <sub>out</sub>	0.1	0.3		mW
Response Time	10%-90%, 1V Prebias I <sub>f</sub> = 100 mA	t <sub>r</sub>		20		nsec
		t <sub>f</sub>		20		nsec
Peak Wavelength	I <sub>f</sub> = 100 mA	λ <sub>p</sub>	1020	1050	1080	nm
Spectral Bandwidth	I <sub>f</sub> = 100 mA	Δλ		145		nm
Electrical Bandwidth	I <sub>f</sub> = 100 mA	BWE		85		MHz